

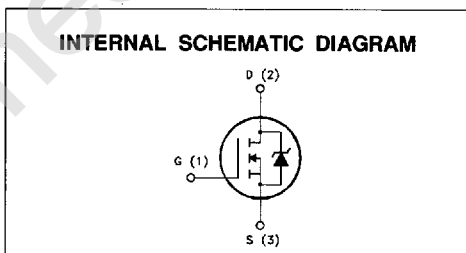
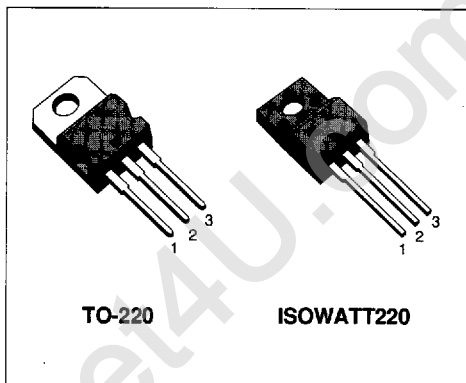
**N - CHANNEL ENHANCEMENT MODE
LOW THRESHOLD POWER MOS TRANSISTOR**

TYPE	V _{DSS}	R _{Ds(on)}	I _D
STP50N05L	50 V	< 0.028 Ω	50 A
STP50N05LFI	50 V	< 0.028 Ω	27 A

- TYPICAL R_{Ds(on)} = 0.024 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- LOGIC LEVEL COMPATIBLE INPUT
- 175°C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP50N05L	STP50N05LFI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	50		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	50		V
V _{GS}	Gate-source Voltage	± 15		V
I _D	Drain Current (continuous) at T _c = 25 °C	50	27	A
I _D	Drain Current (continuous) at T _c = 100 °C	35	19	A
I _{DM} (*)	Drain Current (pulsed)	200	200	A
P _{tot}	Total Dissipation at T _c = 25 °C	150	45	W
	Derating Factor		0.3	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T _{stg}	Storage Temperature	-65 to 175		°C
T _J	Max. Operating Junction Temperature	175		°C

(*) Pulse width limited by safe operating area

THERMAL DATA

			TO-220	ISOWATT220	
R _{thj-case}	Thermal Resistance Junction-case	Max	1	3.33	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max		62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ		0.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose			300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	50	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	400	mJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%)	100	mJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%)	35	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	50			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 125 °C			250 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 15 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1	1.6	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 5 V I _D = 25 A V _{GS} = 5 V I _D = 25 A T _c = 100°C		0.024	0.028 0.056	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	50			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 25 A	17	31		S
C _{ISS}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		2000	2600	pF
C _{OSS}	Output Capacitance			660	900	pF
C _{RSS}	Reverse Transfer Capacitance			160	220	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 25\text{ V}$ $I_D = 25\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 5\text{ V}$ (see test circuit, figure 3)		95 550	140 800	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 40\text{ V}$ $I_D = 50\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 5\text{ V}$ (see test circuit, figure 5)		100		A/ μ s
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80\text{ V}$ $I_D = 50\text{ A}$ $V_{GS} = 5\text{ V}$		42 11 25	60	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Veff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 40\text{ V}$ $I_D = 50\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 5\text{ V}$ (see test circuit, figure 5)		145 215 380	210 310 550	ns ns ns

SOURCE DRAIN DIODE

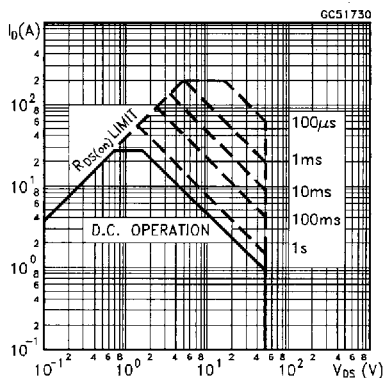
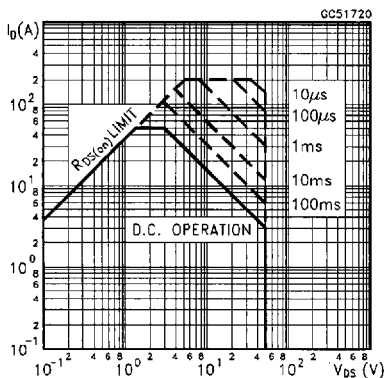
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				50 200	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 50\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 50\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		110		ns
Q_{rr}	Reverse Recovery Charge			0.27		μC
I_{RRM}	Reverse Recovery Current			5		A

(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

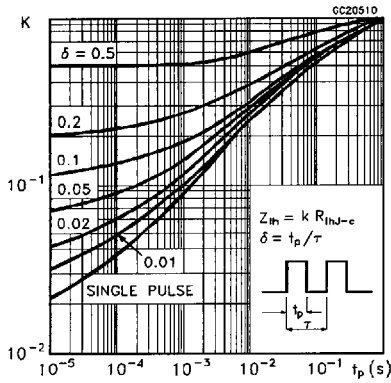
(\bullet) Pulse width limited by safe operating area

Safe Operating Areas For TO-220

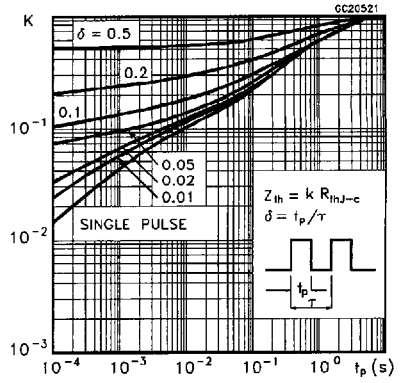
Safe Operating Areas For ISOWATT220



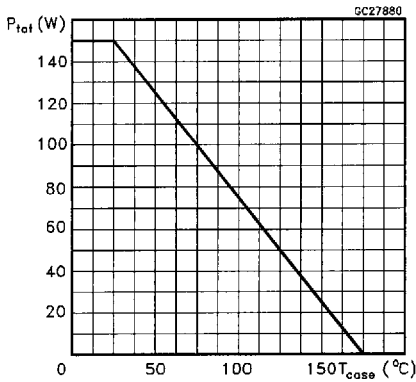
Thermal Impedance For TO-220



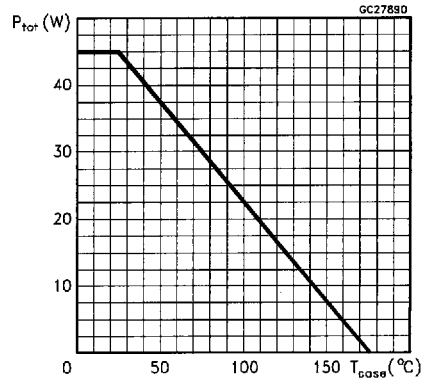
Thermal Impedance For ISOWATT220



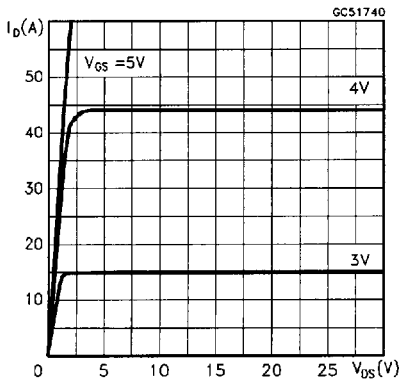
Derating Curve For TO-220



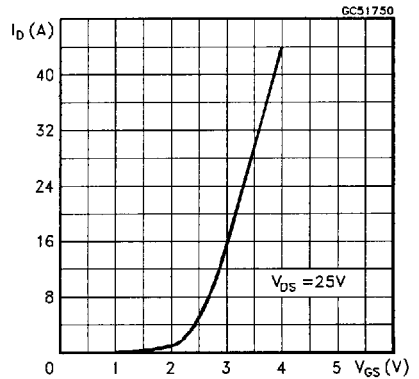
Derating Curve For ISOWATT220



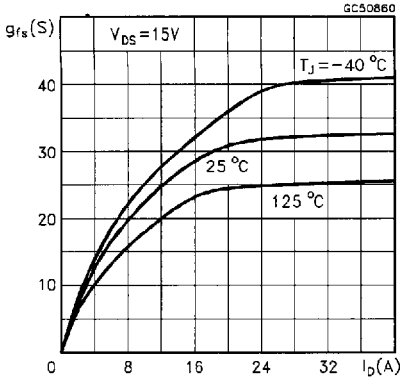
Output Characteristics



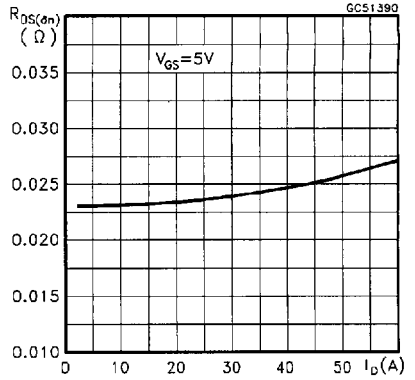
Transfer Characteristics



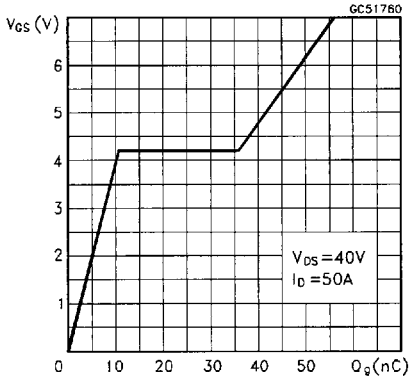
Transconductance



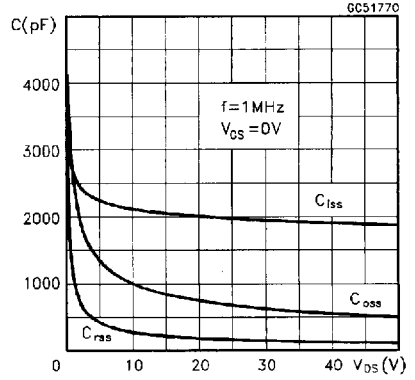
Static Drain-source On Resistance



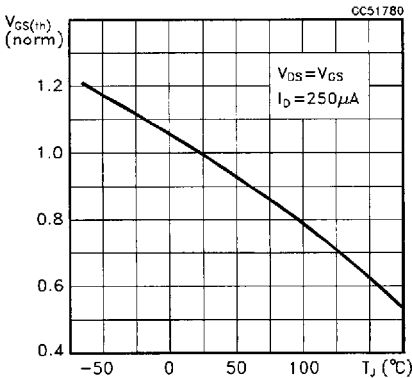
Gate Charge vs Gate-source Voltage



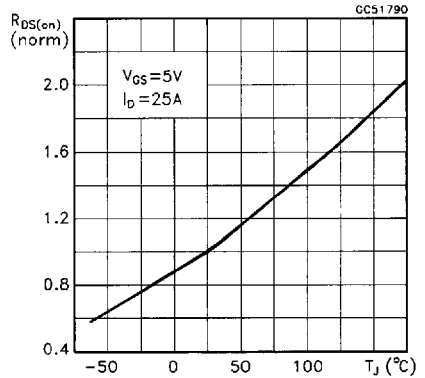
Capacitance Variations



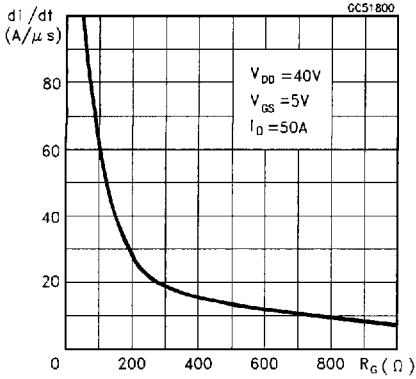
Normalized Gate Threshold Voltage vs Temperature



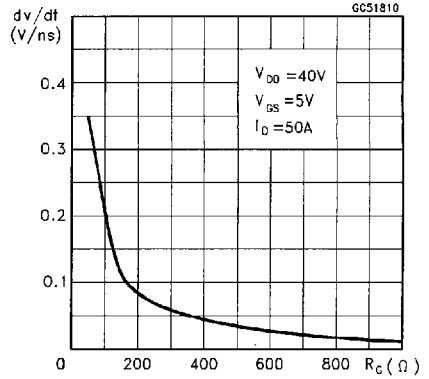
Normalized On Resistance vs Temperature



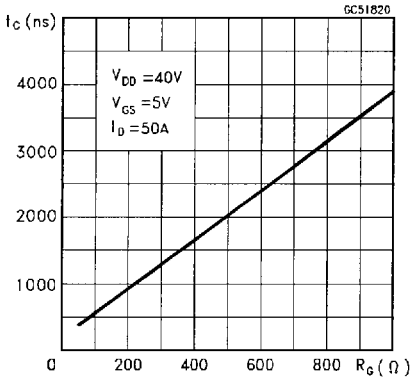
Turn-on Current Slope



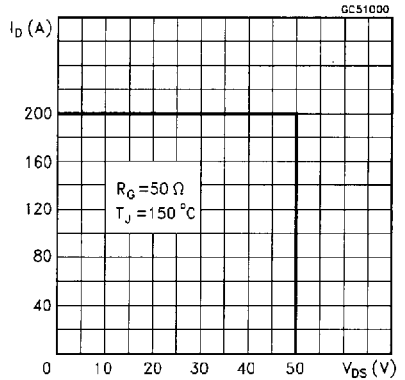
Turn-off Drain-source Voltage Slope



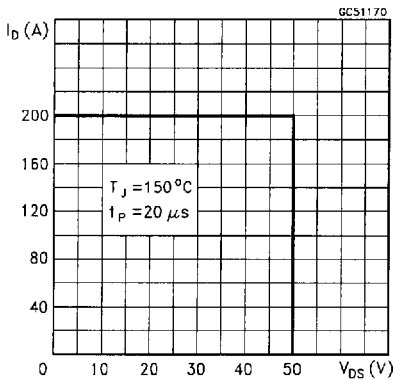
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

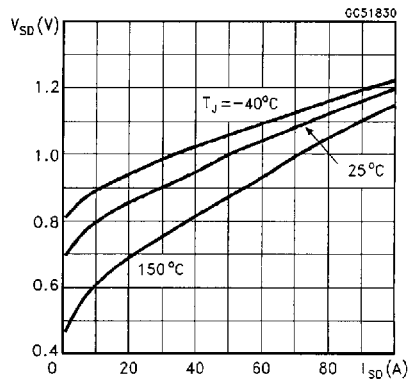


Fig. 1: Unclamped Inductive Load Test Circuits

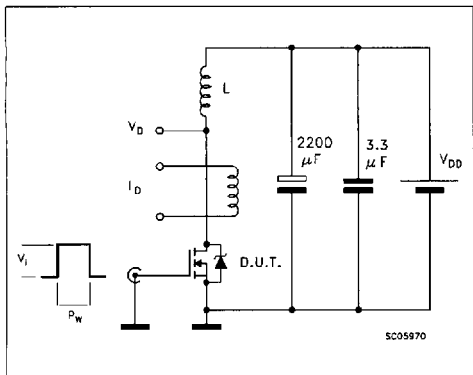


Fig. 2: Unclamped Inductive Waveforms

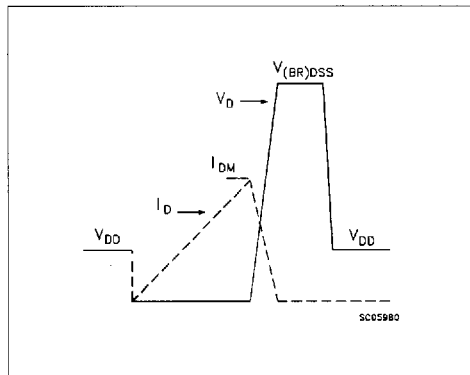


Fig. 3: Switching Times Test Circuits For Resistive Load

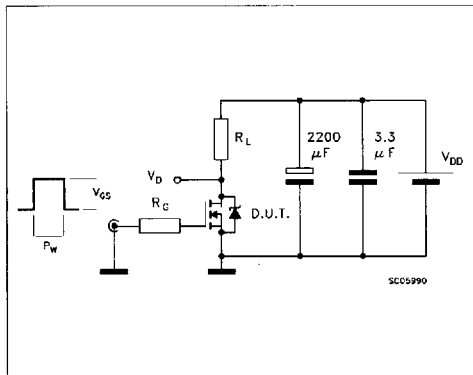


Fig. 4: Gate Charge Test Circuit

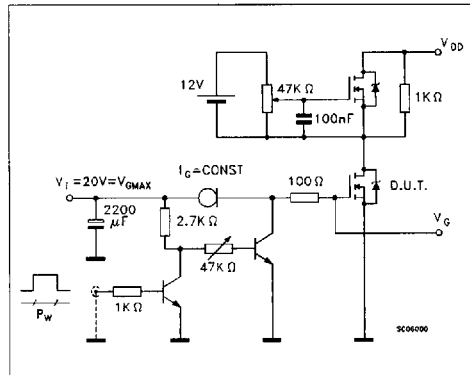


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time

